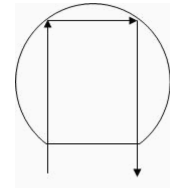
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	WaferVendor
	2.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	{110}+/- 0.5 degree	Wafer Vendor
	4.0	Growth Method	CZ	Wafer Vendor
	5.0	Type	P	Wafer Vendor
	6.0	Dopant	Boron	Wafer Vendor
	7.0	Resistivity	10~30 ohm cm	Wafer Vendor
	8.0	Overall Thickness	1,100.00 +/- 25.00 um	Wafer Vendor
	9.0	Total Thickness Variation (TTV)	<10.00um	Guaranteed by process
	10.0	Orientation	<100> +/-0.5	Wafer Vendor
	11.0	Back Surface Quality	Lapped/Etched	Wafer Vendor
	12.0	Front Surface Quality	Prime	Wafer Vendor
	13.0	Edge Chips	None	Bright Light 100% (note 2)
DeviceSilicon	15.0	Haze	None	Bright Light, 100% (note 2).
	16.0	Scratches	None	Bright Light, 100% (note 2).

Part Number	Customer		
Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

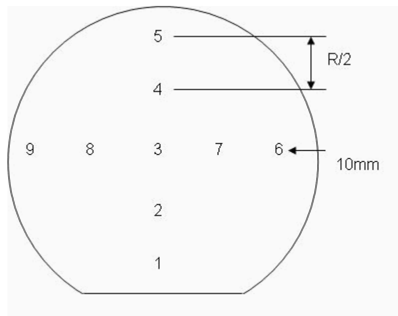
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information